Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	172714	((semiconduct\$4 chip) with (side surface) with (interpos\$4 insulat\$4 spacer spacing laminat\$4 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:03
L2	787	(wafer with semiconduct\$3 with form\$6) and ((semiconduct\$4 wafer) with resist) and (resist with laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:03
L3	787	L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:04
L4	287	1 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:04
L5	14	4 and (mold\$4 mould\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:06
L6	19	4 and (mold\$4 mould\$4 encapsulat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:09
L7	4	6 and interpos\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:23
L8	1	("5597590").PN.	USPAT; USOCR	OR	OFF	2006/05/20 10:23
L9	1	8 and laser with remov\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:25
L11	2	"20040104206"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:42

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L12	1	L11 and interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:35
L13	2	"20020070440"	US-PGPUB;	OR	ON	2006/05/20 11:35
			USPAT;	Samur Yu, Geoffice and Talking the Samura		
Light State of the			EPO; JPO; DERWENT;			
1 2 2			IBM_TDB			
L14	1	13 and resist	US-PGPUB;	OR	ON	2006/05/20 11:39
	_		USPAT; EPO; JPO; DERWENT; IBM_TDB		5	2555/55/25 11:55
L15	1	13 and resist with remov\$4	US-PGPUB;	OR	ON	2006/05/20 11:45
			USPAT;			
			EPO; JPO; DERWENT;		in the control of the	
			IBM_TDB			
L16	1	4 and (mold\$4 with resist)	US-PGPUB;	OR	ON	2006/05/20 11:46
	_	(USPAT; EPO; JPO; DERWENT; IBM_TDB		S.C	2000,03,20 11.10
L17	10	2 and (mold\$4 with resist) not 16	US-PGPUB;	OR	ON	2006/05/20 11:47
		(현대) 보는 사람이 기를 내용하다는 것은 것이라고 함께 하게 되었다고 있다. 	USPAT;			
			EPO; JPO; DERWENT;			
			IBM_TDB			
L18	7	2 and (mold\$4 near5 resist) not 16	US-PGPUB;	OR	ON	2006/05/20 11:47
	•		USPAT;		OI V	2000/03/20 11.4/
			EPO; JPO;			
			DERWENT; IBM_TDB			
S1	2419	semiconductor with interposer	A TO TELEPOOR I	On	ON	2006/05/10 11
31 .	2713	semiconductor with interposer	US-PGPUB; USPAT;	OR	ON	2006/05/18 14:11
			EPO; JPO;	100		
			DERWENT;			
			IBM_TDB			
S2	1235	resist with remov\$5 with laser	US-PGPUB;	OR	ON	2005/12/21 09:00
			USPAT; EPO; JPO;			
			DERWENT; IBM_TDB			
S3	6	S1 and S2	US-PGPUB;	OR	ON	2005/12/21 08:57
			USPAT;			
			EPO; JPO; DERWENT;			
			IBM_TDB			
				<u> </u>		

				,		
S4	341281	semiconductor with (resin plastic insulat\$4 glass ceramic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 09:00
S5	352	S2 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 08:59
S6	917	(resist near5 remov\$5) with laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 09:00
S7	297	S4 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 09:00
S8	96628	semiconductor with surface with (resin plastic insulat\$4 glass ceramic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 09:01
S9	181	S6 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 09:01
S10	8	S6 same S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 09:22
S11	1	("5950071").PN	USPAT; USOCR	OR	OFF	2006/05/20 08:01
S12	2	(("4904498") or ("6866910")).PN.	USPAT; USOCR	OR	OFF	2006/05/18 14:11
S13	1298	resist with remov\$5 with laser	US-PGPUB; USPAT;	OR	ON	2006/05/19 11:39
			EPO; JPO; DERWENT; IBM_TDB			
S14	1	S13 same (encapsulat\$5 with (quick\$4 speed\$4 immediat\$4) with prevent\$4 with (contaminat\$4 oxidat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 11:40

S15	0	b23k026\$.ipc. and (encapsulat\$5 and (quick\$4 speed\$4 immediat\$4) and prevent\$4 and (contaminat\$4 oxidat\$4))	JPO	OR	ON	2006/05/19 11:41
S16	185	b23k026\$.ipc. and ((encapsulat\$5 remov\$4 prevent\$4) and laser and (contaminat\$4 oxidat\$4))	JPO	OR	ON	2006/05/19 11:42
S17	0	b23k026\$.ipc. and (encapsulat\$5 and (remov\$4 prevent\$4) and laser and (contaminat\$4 oxidat\$4))	JPO	OR	ON	2006/05/19 11:44
S18	0	b23k026\$.ipc. and (encapsulat\$5 and laser and (contaminat\$4 oxidat\$4))	JPO	OR	ON	2006/05/19 11:45
S19	17685	b23k026\$.ipc.	JPO	OR	ON	2006/05/19 11:43
S20	5	S19 and encapsulat\$5	JPO	OR	ON	2006/05/19 11:44
S21	365284	h01l021\$.ipc.	JPO	OR	ON	2006/05/19 11:44
S22	638	S21 and encapsulat\$5	JPO	OR	ON	2006/05/19 11:44
S23	0	S21 and (encapsulat\$5 and (remov\$4 prevent\$4) and laser and (contaminat\$4 oxidat\$4))	JPO	OR	ON	2006/05/19 11:45
S24	0	S21 and (encapsulat\$5 and laser and (contaminat\$4 oxidat\$4))	JPO	OR	ON	2006/05/19 11:45
S25	3	S21 and (encapsulat\$5 and (remov\$4 prevent\$4) and laser)	JPO	OR	ON	2006/05/19 11:49
S26	43	S21 and (remov\$4 and (oxid\$9 with prevent\$4) and laser)	JPO	OR	ON	2006/05/19 11:49
S27	9	S21 and (remov\$4 and (oxid\$9 with prevent\$4) and laser) and (mold\$4 resin encapsul\$7 resist)	JPO	OR	ON	2006/05/19 11:52
S28	0	S21 and (remov\$4 with resist and (oxid\$9 with prevent\$4) and laser) and (mold\$4 resin encapsul\$7)	JPO	OR	ON	2006/05/19 11:53
S29	5	S21 and (remov\$4 with resist and (oxid\$9 with prevent\$4) and laser)	JPO	OR	ON	2006/05/19 12:02
S30	80	S21 and (remov\$4 with resist with laser)	JPO	OR	ON	2006/05/19 12:02
S31	1	S30 and (mold\$4 encapsulat\$4 seal\$4 packag\$4)	JPO	OR	ON	2006/05/19 12:04
S32	167	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and (remov\$4 with resist)	JPO	OR	ON	2006/05/19 12:05
S33	1	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and (remov\$4 with resist with laser)	JPO	OR	ON	2006/05/19 12:04

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S34	0	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and (remov\$4 with resist) and laser not S33	JPO	OR	ON	2006/05/19 12:05
S35	478	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and laser not S33	JPO	OR	ON	2006/05/19 12:06
S36	104	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and remov\$4 and laser not S33	JPO	OR	ON	2006/05/19 12:06
S37	76	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and (remov\$4 clean\$4) with laser	JPO	OR	ON	2006/05/19 12:06
S38	87	S21 and (mold\$4 encapsulat\$4 seal\$4 packag\$4) and (remov\$4 clean\$4 etch\$4) with laser	JPO	OR	ON	2006/05/19 12:07
S39	47	S21 and (encapsulat\$4 seal\$4) and (remov\$4 clean\$4 etch\$4) with laser	JPO	OR	ON	2006/05/19 12:07
S40	7	S21 and (encapsulat\$4 seal\$4) and mold\$4 and (remov\$4 clean\$4 etch\$4) with laser	JPO	OR	ON	2006/05/19 12:08
S41	787	(wafer with semiconduct\$3 with form\$6) and ((semiconduct\$4 wafer) with resist) and (resist with laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR (1)	ON	2006/05/20 10:03
S42	2	"20040104206"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:42
S43	1	S42 and interpos\$4	US-PGPUB; USPAT;	OR	ON	2006/05/20 08:14
			EPO; JPO; DERWENT;			
			IBM_TDB			
S44	3791	228/179.1-180.22.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:15
S45	132	228/138.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:15

S46	1	S44 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:21
S47	38858	(ball grid ballgrid) near3 array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:22
S48	235727	((semiconduct\$4 chip) with (side surface) with (interpos\$4 insulat\$4 spac\$3 laminat\$4 layer\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 10:02
S49	279	S41 and S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:32
S50	28	((wafer with semiconduct\$3 with form\$6) and ((semiconduct\$4 wafer) with resist) and (resist with laser)) same (((semiconduct\$4 chip) with (side surface) with (interpos\$4 insulat\$4 spac\$3 laminat\$4 layer\$4)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:33
S51	481647	"28" and (mold\$4 mould\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:34
S53	15	S49 and (mold\$4 mould\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 09:18
S54	11358	(mold\$4 mould\$4) with (clean\$4 remov\$4 ablat\$4) with (textur\$4 rough\$5 grip\$4 adher\$7 adhes\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:44
S55	21	(mold\$4 mould\$4) with (clean\$4 remov\$4 ablat\$4) with ((textur\$4 rough\$5 grip\$4 adher\$7 adhes\$5) near5 laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 09:00

						
S56	2	S55 and (resist with (semiconduct\$5 wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:47
S57	3	S55 and resist not S56	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:48
S58	16	S55 not S56 not S57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:49
S59	1	("6399177").PN.	USPAT; USOCR	OR	OFF	2006/05/20 08:49
S60	1	S59 and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:50
S61	1	S59 and rough\$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:50
S62	0	S59 and ablat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:51
S63	1	S59 and textur\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 08:51
S64	2	"20030207574"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 09:00
S65	2	(("6031249") or ("6278132")).PN.	USPAT; USOCR	OR	OFF	2006/05/20 09:18
S66	0	S53 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 09:19

S67	2	S49 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT:	OR	ON	2006/05/20 09:19
			DERWENT; IBM_TDB			